## KSH13005DT

对应国外型号 FJP5304D

## ■ 主要用途

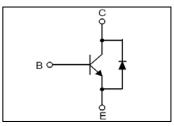
高压快速开关。电子镇流器、电子变压器等应用。

## **■ 极限值** (T<sub>a</sub>=25℃)

T <sub>stg</sub> ——贮存温度······ -55~150℃
Tj──结温······ 150℃
P <sub>C</sub> ——集电极功率耗散(T <sub>c</sub> =25℃)
V <sub>CBO</sub> ——集电极—基极电压······ 700V
V <sub>CEO</sub> ——集电极—发射极电压 400V
V <sub>EBO</sub> ——发射极—基极电压 9V
I <sub>C</sub> ——集电极电流(DC)
I <sub>C</sub> ——集电极电流(脉冲) … 8A
I <sub>B</sub> ——基极电流······2A

## ■ 外形图及引脚排列





#### **■ 电参数** (T<sub>a</sub>=25°C)

参数符号	符号说明	最小值	典型值	最大值	单 位	测试条件
ВУсво	集电极一基极击穿电压	700			V	Ic=1mA, IE=0
BVCEO	集电极一发射极击穿电压	400			V	Ic=5mA, I <sub>B</sub> =0
BVebo	发射极—基极击穿电压	9			V	$I_E=1$ mA, $I_C=0$
Ієво	发射极—基极截止电流			1	mA	V <sub>EB</sub> =9V, I <sub>C</sub> =0
hfe	直流电流增益	10		40		Vce=5V, Ic=1A
		8		40		Vce=5V, Ic=2A
VCE (sat)	集电极一发射极饱和电压			0. 5	V	Ic=1A, I <sub>B</sub> =0. 2A
				0.8	V	Ic=2A, IB=0.5A
				1	V	Ic=4A, IB=1A
VBE(sat)	基极一发射极饱和电压			1. 2	V	Ic=1A, IB=0.2A
				1.6	V	Ic=2A, IB=0.5A
$V_{\mathrm{F}}$	内部二极管正向压降			2. 5	V	I <sub>F</sub> =2A
Cob	共基极输出电容		65		pF	VcB=10V, f=0.1MHz
ton	导通时间			0.8	μs	→ Vcc=125V, Ic=2A,
ts	载流子贮存时间			4	μs	► I <sub>B1</sub> =-I <sub>B2</sub> =0. 4A
tf	下降时间			0. 9	μs	J
ts	贮存时间	2		5	μs	VcE=5V, Ic=0.5A(UI9600)

分档: H1(10--16) H2(14--21) H3(19--26) H4(24--31) H5(29--40)

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#### ■ 特性曲线

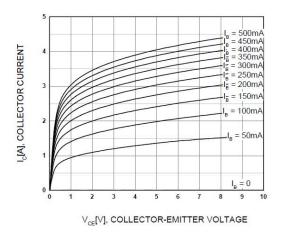


Figure 1. Static Characteristic

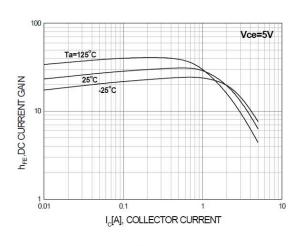


Figure 2. DC Current Gain

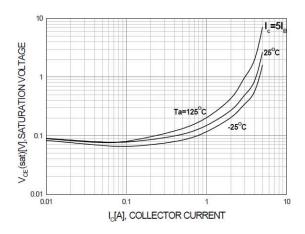


Figure 3. Collector-Emitter Saturation Voltage

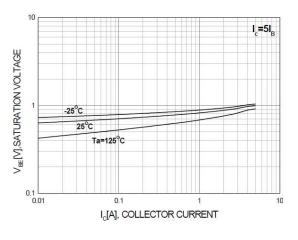


Figure 4. Base-Emitter Saturation Voltage

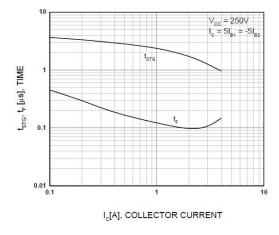


Figure 5. Resitive Load Switching Time

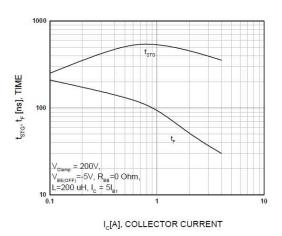


Figure 6. Inductive Load Switching Time

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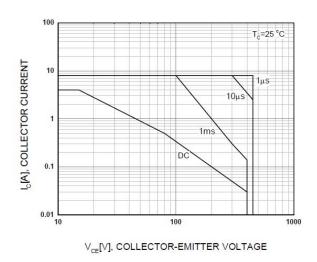


Figure 7. Forward Bias Safe Operating Area

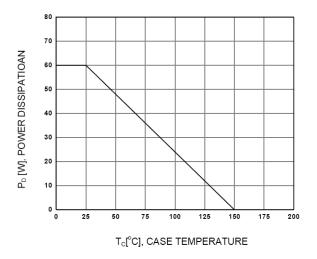


Figure 9. Power Derating

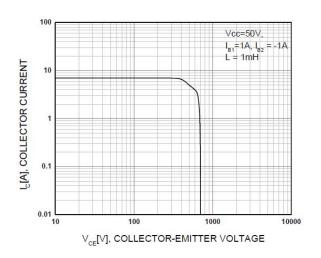


Figure 8. Reverse Bias Safe Operating Area